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Attracting method

Abstract

A method of attracting an object to a mounting table is provided. The object is a substrate, an edge ring, or a combination of the substrate and the edge ring. The mounting table is provided with an electrostatic chuck including electrodes. After the object is placed on the electrostatic chuck, n-phase alternating current (AC) voltages ($n \geq 2$) are applied to the electrodes. Each phase voltage of the n-phase AC voltages has a phase different from each other, and the phase voltage of the n-phase AC voltages is applied based on a self-bias voltage of the object.

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Background/Summary

CROSS-REFERENCE TO RELATED APPLICATIONS (1) This application is a divisional application of and claims the benefit under 35 U.S.C. § 120 of U.S. patent application Ser. No. 17/077,241, filed Oct. 22, 2020, which claims priority to Japanese Patent Application No. 2019-

TECHNICAL FIELD

(1) The present disclosure relates to an attracting method, a mounting table, and a plasma processing apparatus.

BACKGROUND

(2) In processing apparatuses that apply desired treatment, such as etching, on a substrate, a mounting table that attracts the substrate is known.

(3) Patent Document 1 describes an electrostatic chuck device to which alternating current voltages (AC voltages) are applied. As the AC voltages applied to the electrostatic chuck device, n-phase AC voltages ($n \geq 2$) are applied. The electrostatic chuck device includes a sample stage and a circuit for applying the n-phase AC voltages. The sample stage includes electrodes to which the n-phase AC voltages are applied and an insulator for insulating the electrodes from each other.

RELATED ART DOCUMENT

Patent Document

(4) [Patent Document 1] Japanese Laid-open Patent Application Publication No. 2003-332412

SUMMARY

(5) In one aspect, the present disclosure provides an attracting method, a mounting table, and a plasma treatment apparatus that suppress reduction of attractive force.

(6) In one aspect, a method of attracting an object to a mounting table is provided. The object is a substrate, an edge ring, or a combination of the substrate and the edge ring. The mounting table is provided with an electrostatic chuck including electrodes. After the object is placed on the electrostatic chuck, n-phase alternating current (AC) voltages ($n \geq 2$) are applied to the electrodes. Each phase voltage of the n-phase AC voltages has a phase different from each other, and the phase voltage of the n-phase AC voltages is applied based on a self-bias voltage of the object.

Description

BRIEF DESCRIPTION OF THE DRAWINGS

(1) FIG. 1 is a cross-sectional diagram illustrating an example of a plasma processing apparatus according to an embodiment;

(2) FIGS. 2A and 2B are diagrams illustrating an example of an arrangement of electrodes in an electrostatic chuck;

(3) FIG. 3A is a graph illustrating an example of three-phase AC voltages applied to the electrodes;

(4) FIG. 3B is a graph illustrating an example of a sum of attractive force when the three-phase AC voltages are applied;

(5) FIG. 4A is a graph illustrating an example of two-phase AC voltages applied to the electrodes;

(6) FIG. 4B is a graph illustrating an example of a sum of attractive force when the two-phase AC voltages are applied; and

(7) FIGS. 5A and 5B are graphs illustrating examples of a relationship between applied voltage and a flow rate of a heat transfer gas.

DETAILED DESCRIPTION OF EMBODIMENTS

(8) Hereinafter, embodiments for carrying out the present disclosure will be described with reference to the drawings. Note that in the drawings, elements having substantially identical features are given to the same reference symbols, and redundant descriptions will be omitted.

(9) <Plasma Processing Apparatus>

(10) A plasma processing apparatus 1 according to an embodiment will be described with reference to FIG. 1. FIG. 1 is a cross-sectional diagram illustrating an example of the plasma processing apparatus 1 according to the present embodiment. The plasma processing apparatus 1 according to

the present embodiment is a capacitively coupled parallel plate processing apparatus, and includes a chamber **10**. The chamber **10** is a cylindrical container formed of, for example, aluminum having a surface treated by anodic oxidation, and is grounded.

(11) A cylindrical support platform **14** is disposed at the bottom of the chamber **10**, via an insulating plate **12** made of ceramic or the like. On the support platform **14**, for example, a mounting table **16** is provided. The mounting table **16** includes an electrostatic chuck **20** and a base **16a**, and a wafer W is placed on the upper surface of the electrostatic chuck **20**. An annular edge ring **24** made of silicon or the like is disposed around the wafer W. The edge ring **24** may also be referred to as a focus ring. The edge ring **24** is an example of an outer peripheral member disposed around the mounting table **16**. Around the base **16a** and the support platform **14**, an annular insulator ring **26** made of quartz or the like is provided. Inside the electrostatic chuck **20**, a first electrode **20a** formed of a conductive film is embedded in an insulating layer **20b** and is provided near the center of the electrostatic chuck **20**. The first electrode **20a** is connected to a power supply **22**. Because voltage applied from the power supply **22** to the first electrode **20a** causes a potential difference between the surface of the electrostatic chuck **20** and the wafer W which is an object to be attracted, the wafer W as the object to be attracted is attracted to the surface of the electrostatic chuck **20**. In addition, inside the electrostatic chuck **20**, a second electrode **20c** made of a conductive film is embedded in the insulating layer **20b** and is provided at the outer circumferential side of the electrostatic chuck **20**. The second electrode **20c** is connected to a power supply **23**. Because voltage applied from the power supply **23** to the second electrode **20c** causes a potential difference between the surface of the electrostatic chuck **20** and the edge ring **24** which is an object to be attracted, the edge ring **24** as the object to be attracted is attracted to the surface of the electrostatic chuck **20**. The electrostatic chuck **20** may include a heater to control temperature.

(12) Inside the support platform **14**, a refrigerant chamber **28** is formed, for example, in the form of a ring or a vortex. A refrigerant at a predetermined temperature, such as cooling water, is supplied from the chiller unit (not illustrated), passes through a pipe **30a**, the refrigerant chamber **28**, and a pipe **30b**, and is returned to the chiller unit. As the refrigerant circulates through such a path, the temperature of the wafer W can be controlled by the temperature of the refrigerant. In addition, a heat transfer gas, e.g., He gas, which is supplied from a heat transfer gas supply mechanism (not illustrated), is supplied to a gap between the surface of the electrostatic chuck **20** and the back surface of the wafer W, through a gas supply line **32**. As this heat transfer gas increases the heat transfer coefficient between the surface of the electrostatic chuck **20** and the back surface of the wafer W, the temperature of the wafer W can be controlled by the temperature of the refrigerant more effectively. In addition, in a case in which the electrostatic chuck **20** is equipped with a heater, heating by the heater and cooling by the refrigerant enable high responsiveness and high precision control of the temperature of the wafer W. The plasma processing apparatus **1** may be configured such that the heat transfer gas, e.g., He gas, supplied from the heat transfer gas supply mechanism (not illustrated) is also supplied to a gap between the surface of the electrostatic chuck **20** and the back surface of the edge ring **24** through another gas supply line (not illustrated). In addition, by controlling the pressure of He gas supplied to the gap between the surface of the electrostatic chuck **20** and the back surface of the object to be attracted (wafer W and/or edge ring **24**), heat transfer characteristics of the electrostatic chuck **20** and the object (wafer W and/or edge ring **24**) may be controlled, and the temperature of the object (wafer W and/or edge ring **24**) may be controlled.

(13) An upper electrode **34** is provided on the ceiling of the chamber **10** so as to face the mounting table **16**. A space between the upper electrode **34** and the mounting table **16** is a plasma processing space. The upper electrode **34** occludes an opening of the ceiling of the chamber **10** via a shielding member **42** of an insulating material. The upper electrode **34** has an electrode plate **36** and an electrode support **38**. The electrode plate **36** is formed of a silicon-containing material such as silicon or SiC, and a large number of gas discharge holes **37** are formed on the surface of the electrode plate **36** facing the mounting table **16**. The electrode support **38** removably supports the

electrode plate **36**, and is formed of a conductive material, such as aluminum having a surface treated by anodic oxidation. Inside the electrode support **38**, a number of gas flow holes **41a** and a number of gas flow holes **41b** extend downward from gas diffusion chambers **40a** and **40b** respectively, and communicate with the gas discharge holes **37**.

(14) A gas inlet **62** is connected to a process gas supply **66** via a gas supply line **64**. The gas supply line **64** is provided with a mass flow controller (MFC) **68** and an open/close valve **70** from the upstream side where the process gas supply **66** is located. A process gas is supplied from the process gas supply **66**, and flow of the process gas is controlled by the mass flow controller **68** and the open/close valve **70**. The process gas is supplied to the gas diffusion chambers **40a** and **40b** through the gas supply line **64**, passes through the gas flow holes **41a** and **41b**, and is discharged into the plasma processing space from the gas discharge holes **37** of the upper electrode **34**. That is, the upper electrode **34** functions as a showerhead for supplying gas.

(15) The plasma processing apparatus **1** includes a first radio frequency power supply **90** and a second radio frequency power supply **48**. The first radio frequency power supply **90** is a power source that generates first radio frequency power (hereinafter referred to as “HF power”). The first radio frequency power has a frequency suitable for generating a plasma. The frequency of the first radio frequency power is, for example, in a range of 27 MHz to 100 MHz. The first radio frequency power supply **90** is connected to the base **16a** via a matcher **88** and a power supply line **89**. The matcher **88** includes circuitry for causing the output impedance of the first radio frequency power supply **90** to match impedance of a load side (base **16a** side). The first radio frequency power supply **90** may be connected to the upper electrode **34** via the matcher **88**.

(16) The second radio frequency power supply **48** is a power source that generates second radio frequency power (hereinafter referred to as “LF power”). The second radio frequency power has a frequency lower than the frequency of the first radio frequency power. In a case in which the second radio frequency power is used in conjunction with the first radio frequency power, the second radio frequency power is used as radio frequency power for biasing in order to draw ions into the wafer **W**. The frequency of the second radio frequency power is, for example, in a range of 400 kHz to 13.56 MHz. The second radio frequency power supply **48** is connected to the base **16a** via a matcher **46** and a power supply line **47**. The matcher **46** includes circuitry for causing the output impedance of the second radio frequency power supply **48** to match impedance of the load side (base **16a** side). According to the above-described configuration, the mounting table **16** also functions as a lower electrode. Note that pulsed DC may be used as electric power for biasing in order to draw ions to the wafer **W**. In this case, the plasma processing apparatus **1** has a pulsed DC power supply (not illustrated) instead of the second radio frequency power supply **48**. The pulsed DC power supply is connected to the base **16a** via the power supply line **47**. Alternatively, a composite wave in which multiple input voltage, such as pulsed DC (rectangular wave) and a triangular wave, are combined may be used as power for biasing to draw ions into the wafer **W**. In this case, the plasma processing apparatus **1** has a power supply that outputs the composite wave (not illustrated), instead of the second radio frequency power supply **48**. The power supply for outputting the composite wave is connected to the base **16a** via the power supply line **47**.

(17) It should be noted that a plasma may be generated using the second radio frequency power without using a first radio frequency power. That is, a plasma may be generated by using only a single type of radio frequency power. In this case, the frequency of the second radio frequency power may be greater than 13.56 MHz, for example, 40 MHz. The plasma processing apparatus **1** may not include the first radio frequency power supply **90** and the matcher **88**. The mounting table **16** serves as a lower electrodes. The upper electrode **34** serves a showerhead that supplies the gas.

(18) A second variable power supply **50** is connected to the upper electrode **34**, and applies DC voltage to the upper electrode **34**. A first variable power supply **55** is connected to the edge ring **24**, and applies DC voltage to the edge ring **24**. The thickness of a sheath on the edge ring **24** is controlled, by applying DC voltage of a predetermined magnitude that is determined in accordance

with an amount of abrasion of the edge ring **24**, from the first variable power supply **55** to the edge ring **24**. This eliminates a level difference between a sheath on the edge ring **24** and a sheath on the wafer **W**, and therefore an angle of incidence of ions that are incident on the wafer **W** is prevented from becoming oblique at the edge of the wafer **W**. As a result, this avoids occurrence of tilting, in which the shape of a recess formed on the wafer **W** becomes oblique.

(19) A DC voltage detector **57** is also provided to measure the voltage of the edge ring **24**. The DC voltage detector **57** is connected, via a switching device **56**, to a wire that connects the first variable power supply **55** to the edge ring **24** at an intermediate segment of the wire. The switching device **56** is provided at the intermediate segment of the wire, and is configured to switch between a first state in which the edge ring **24** is electrically connected to the first variable power supply **55** and a second state in which the edge ring **24** is electrically connected to the DC voltage detector **57**. By switching the switching device **56** to the first state, voltage can be applied to the edge ring **24** from the first variable power supply **55**. By switching the switching device **56** to the second state, voltage of the edge ring **24** as a cathode (i.e., potential difference between the edge ring **24** and the ground) incurred due to difference in moving speed between electron and ion during plasma processing, can be detected. The voltage (more precisely, DC component of the voltage) incurred due to difference in moving speed between electron and ion during plasma processing may be referred to as “DC self-bias voltage” (or “self-bias voltage”). In the following description, self-bias voltage of an object (e.g., edge ring **24** or wafer **W**) to be attracted by the electrostatic chuck **20** may be denoted by “V_{dc}”.

(20) An exhaust device **84** is connected to an exhaust pipe **82**. The exhaust device **84** includes a vacuum pump such as a turbomolecular pump, which evacuates via the exhaust pipe **82** from an exhaust port **80** formed at the bottom of the chamber **10** to reduce the pressure in the chamber **10** to a desired degree of vacuum. The exhaust device **84** also controls the pressure in the chamber **10** to be constant while using a value of a pressure gauge (not illustrated) to measure the pressure in the chamber **10**. A loading/unloading port **85** is provided at the side wall of the chamber **10**. The wafer **W** is loaded into and unloaded from the loading/unloading port **85** by opening and closing a gate valve **86**.

(21) An annular baffle plate **83** is disposed between the outer side surface of the insulator ring **26** and the inner side wall of the chamber **10**. The baffle plate **83** is provided with multiple through-holes, and is formed of aluminum. The surface of the baffle plate **83** is coated with ceramic such as Y.sub.2O.sub.3.

(22) When performing predetermined plasma processing, such as plasma etching, in the plasma processing apparatus **1** according to the above-described configuration, the gate valve **86** is opened, and the wafer **W** is loaded into the chamber **10** through the loading/unloading port **85**. The wafer **W** loaded into the chamber **10** is placed on the wafer mounting surface of the electrostatic chuck **20**, and the gate valve **86** is closed. Also, on the edge ring mounting surface of the electrostatic chuck **20**, the edge ring **24** is placed. A process gas is supplied to the interior of the chamber **10**, and the interior of the chamber **10** is evacuated by the exhaust device **84**.

(23) The first radio frequency power and the second radio frequency power are applied to the mounting table **16**. The power supply **22** then applies voltage to the first electrode **20a** of the electrostatic chuck **20** to attract the wafer **W** to the wafer mounting surface of the electrostatic chuck **20**. The power supply **23** also applies voltage to the second electrode **20c** of the electrostatic chuck **20** to attract the edge ring **24** to the edge ring mounting surface of the electrostatic chuck **20**. Note that DC voltage may be applied from the second variable power supply **50** to the upper electrode **34**.

(24) Plasma processing, such as etching, is applied to the surface of the wafer **W** to be processed by means of radicals or ions in a plasma generated in the plasma processing space.

(25) The plasma processing apparatus **1** is provided with a controller **200** that controls operations of an entirety of the plasma processing apparatus **1**. A central processing unit (CPU) provided in the

controller **200** performs desired plasma processing, such as etching, in accordance with a recipe stored in a memory such as a ROM or a RAM. The recipe may include control information of the plasma processing apparatus **1** with respect to a process condition, such as processing time, pressure (gas exhaust), first and second radio frequency power or voltage, and various gas flow rates. The recipe may also include information about temperatures in the chamber (e.g., upper electrode temperature, chamber sidewall temperature, wafer W temperature, and electrostatic chuck temperature), a temperature of the refrigerant output from the chiller, and the like. A program and the recipe representing these process conditions may be stored in a hard disk drive or a semiconductor memory. The recipe may also be stored in a removable computer-readable storage medium such as a CD-ROM, a DVD, or the like, and by the portable computer-readable storage medium being loaded in a predetermined location, the recipe may be read from the portable computer-readable storage medium.

(26) Next, arrangement of electrodes in the electrostatic chuck **20** on the mounting table **16** will be further described with reference to FIGS. **2A** and **2B**. FIG. **2A** is a plan view illustrating an example of arrangement of the first electrode **20a** in the wafer mounting surface of the electrostatic chuck **20**. FIG. **2B** is a plan view illustrating an example of arrangement of the second electrode **20c** in the edge ring mounting surface of the electrostatic chuck **20**.

(27) As illustrated in FIG. **2A**, the first electrode **20a** at the wafer mounting surface includes three electrodes. In the present embodiment, these three electrodes are referred to as an electrode **20a1**, an electrode **20a2**, and an electrode **20a3**, respectively. Each of the electrodes **20a1**, **20a2**, and **20a3** has a generally fanned planar shape, and the electrodes **20a1**, **20a2**, and **20a3** are arranged in a circumferential direction with respect to the central axis of the electrostatic chuck **20**. The power supply **22** is connected to the electrodes **20a1**, **20a2**, and **20a3**. The power supply **22** generates alternating current (AC) voltages (i.e., n-phase AC voltages ($n \geq 2$)).

(28) As illustrated in FIG. **2B**, the second electrode **20c** at the edge ring mounting surface includes three electrodes, electrodes **20c1**, **20c2**, and **20c3**. Each of the electrodes **20c1**, **20c2**, and **20c3** has a shape like an arc, and the electrodes **20c1**, **20c2**, and **20c3** are arranged in the circumferential direction with respect to the central axis of the electrostatic chuck **20**. The power supply **23** is connected to the electrodes **20c1**, **20c2**, and **20c3**. The power supply **23** generates AC voltages (i.e., n-phase AC voltages ($n \geq 2$)).

(29) Although the configuration in which the electrodes (electrodes **20a1**, **20a2**, and **20a3**) in the first electrode **20a** are arranged in a circumferential direction has been described above, arrangement of the electrodes is not limited thereto. The electrodes may be arranged in a radial direction. Further, although the configuration in which the electrodes (electrodes **20c1**, **20c2**, and **20c3**) in the second electrode **20c** are arranged in a circumferential direction has been described above, arrangement of the electrodes is not limited thereto. The electrodes may be arranged in a radial direction.

(30) Next, three-phase AC voltages applied to the second electrode **20c** (electrodes **20c1**, **20c2**, and **20c3**) will be described with reference to FIG. **3A**. FIG. **3A** is a graph illustrating an example of the three-phase AC voltages applied to the electrodes **20c1**, **20c2**, and **20c3**. The vertical axis indicates voltage (phase voltage) applied to the electrodes **20c1**, **20c2**, and **20c3** (note that the voltage applied to the electrodes may also be referred to as “applied voltage”), and the horizontal axis indicates time. In the description of the present embodiment, unless otherwise stated, “voltage” at a certain point (or voltage applied to the certain point) refers to a potential difference (voltage) between the certain point and the ground. An example of the AC voltage (phase voltage) applied to the electrode **20c1** is illustrated in a solid line curve, an example of the AC voltage (phase voltage) applied to the electrode **20c2** is illustrated in a dashed-dotted line curve, and an example of the AC voltage (phase voltage) applied to the electrode **20c3** is illustrated in a broken line curve. The amplitude of each of the applied voltages is normalized to 1.

(31) In the present embodiment, the AC voltage (phase voltage) applied to each of the electrodes

20c1, **20c2**, and **20c3** from the power supply **23** has the same peak amplitude, the same frequency, and a phase different from each other. For example, the phase difference between the AC voltages applied to the electrodes **20c1**, **20c2**, and **20c3** is set to 120° .

(32) Also, the AC voltages (phase voltages) applied to the electrodes **20c1**, **20c2**, and **20c3** from the power supply **23** are determined based on the self-bias voltage V_{dc} of the edge ring **24**. For example, the AC voltages on the basis of the self-bias voltage V_{dc} of the edge ring **24** are applied to the electrodes **20c1**, **20c2**, and **20c3** from the power supply **23**. In other words, an average value of the voltage applied from the power supply **23** to each of the electrodes **20c1**, **20c2**, and **20c3** is shifted by the magnitude of the self-bias voltage V_{dc} of the edge ring **24**. In other words, the AC voltage applied from the power supply **23** to each of the electrodes **20c1**, **20c2**, and **20c3** is obtained by superimposing, on an AC component, a negative DC voltage component having a magnitude based on the magnitude of the self-bias voltage V_{dc} of the edge ring **24** (i.e., the AC voltage applied from the power supply **23** to each of the electrodes **20c1**, **20c2**, and **20c3** is made by offsetting an AC component by the magnitude of the negative DC voltage component based on the self-bias voltage V_{dc} of the edge ring **24**). FIG. 3A illustrates a case in which the AC voltages applied are offset by -0.2 (i.e., the self-bias voltage V_{dc} of the edge ring **24** is -0.2).

(33) The magnitude of self-bias voltage V_{dc} of the edge ring **24** is detected by, for example, the DC voltage detector **57**. A method of detecting the magnitude of the self-bias voltage V_{dc} is not limited thereto, and other methods may be used. Alternatively, a predetermined value may also be used as the magnitude of the self-bias voltage V_{dc} . For example, the self-bias voltage V_{dc} may be obtained in advance through experiments, simulations, or the like, and the self-bias voltage V_{dc} obtained in advance may be stored, as the predetermined value, in the memory of the controller **200**.

Alternatively, the relationship between self-bias voltage V_{dc} and a plasma generation condition (e.g., LF power used as the radio frequency power for biasing) may be determined in advance, and the self-bias voltage V_{dc} may be estimated based on the relationship and the plasma generation conditions.

(34) The attractive force generated in the edge ring **24** when three-phase AC voltages illustrated in FIG. 3A are applied to the second electrode **20c** (electrodes **20c1**, **20c2**, and **20c3**) is described with reference to FIG. 3B. FIG. 3B is a graph illustrating an example of a sum of attractive force generated in the edge ring **24** when the three-phase AC voltages are applied to the electrodes **20c1**, **20c2**, and **20c3**. The vertical axis indicates the sum of the attractive force and the horizontal axis indicates time. As illustrated in FIG. 3B, the attractive force of the mounting table **16** for attracting the edge ring **24** can be made constant.

(35) In addition, with respect to the first electrode **20a** (electrodes **20a1**, **20a2**, and **20a3**), by applying the three-phase AC voltages as illustrated in FIG. 3A to the first electrode **20a** (electrodes **20a1**, **20a2**, and **20a3**), similar to the case of the second electrode **20c** (electrodes **20c1**, **20c2**, and **20c3**), the attractive force for attracting the wafer **W** to the mounting table **16** can be made constant as illustrated in FIG. 3B.

(36) The AC voltages (phase voltages) applied to the electrodes **20a1**, **20a2**, and **20a3** from the power supply **22** are determined based on the self-bias voltage V_{dc} of the wafer **W**. For example, AC voltages on the basis of the self-bias voltage V_{dc} of the wafer **W** are applied to the electrodes **20a1**, **20a2**, and **20a3** from the power supply **22**. In other words, an average value of the voltage applied from the power supply **22** to each of the electrodes **20a1**, **20a2**, and **20a3** is shifted by the magnitude of the self-bias voltage V_{dc} of the wafer **W**. In other words, the AC voltage applied from the power supply **22** to each of the electrodes **20a1**, **20a2**, and **20a3** is obtained by superimposing, on an AC component, a negative DC voltage component based on the self-bias voltage V_{dc} of the wafer **W** (i.e., the AC voltage applied from the power supply **22** to each of the electrodes **20a1**, **20a2**, and **20a3** is made by offsetting an AC component by the magnitude of the negative DC voltage component based on the self-bias voltage V_{dc} of the wafer **W**).

(37) A DC voltage detector (not illustrated) for detecting the self-bias voltage V_{dc} of the wafer **W**

may be provided. Alternatively, a predetermined value may also be used as the magnitude of the self-bias voltage V_{dc} . For example, the self-bias voltage V_{dc} may be obtained in advance through experiments, simulations, or the like, and the self-bias voltage V_{dc} obtained in advance may be stored, as the predetermined value, in the memory of the controller **200**. Alternatively, the relationship between self-bias voltage V_{dc} and a plasma generation condition (e.g., LF power) may be determined in advance, and the self-bias voltage V_{dc} may be estimated based on the relationship and the plasma generation condition. In another embodiment, the relationship between self-bias voltage of the edge ring **24** and self-bias voltage of the wafer W may be obtained in advance, and the self-bias voltage of the wafer W may be estimated based on the relationship and the self-bias voltage of the edge ring **24** detected by the DC voltage detector **57**.

(38) In the above description with reference to FIGS. **2A** to **3B**, a case, in which both the number of electrodes in the first electrode **20a** and the number of electrodes in the second electrode **20c** are three, is described. However, the present invention is not limited thereto. Each of the first electrode **20a** and the second electrode **20c** may have two electrodes, or may have four or more electrodes. Also, a case in which the number of electrodes in the first electrode **20a** is the same as the number of electrodes in the second electrode **20c** has been described above, but the number of electrodes in the first electrode **20a** and the number of electrodes in the second electrode **20c** may differ.

(39) A case in which the number of electrodes in the second electrode **20c** is two will be further described with reference to FIGS. **4A** and **4B**. FIG. **4A** is a graph illustrating an example of two-phase AC voltages applied to the electrodes when the number of the electrodes in the second electrode **20c** is two. The vertical axis indicates applied voltage, and the horizontal axis indicates time. An example of AC voltage applied to a first electrode in the second electrode **20c** is illustrated in solid line curve, and an example of AC voltage applied to a second electrode in the second electrode **20c** is illustrated in dashed-dotted line curve. The amplitude of the applied voltages is normalized to 1.

(40) The AC voltages applied to the electrodes in the second electrode **20c** from the power supply **23** have the same peak amplitude and the same frequency, and there is a phase difference between the AC voltages. For example, the phase difference of the AC voltages applied to the electrodes in the second electrode **20c** is set to 90° . Also, the AC voltages applied to the electrodes in the second electrode **20c** from the power supply **23** are determined based on the self-bias voltage V_{dc} of the edge ring **24**. For example, the AC voltages on the basis of the self-bias voltage V_{dc} of the edge ring **24** are applied to the electrodes in the second electrode **20c** from the power supply **23**. In other words, an average value of voltage applied to each of the electrodes in the second electrode **20c** from the power supply **23** is shifted by the magnitude of the self-bias voltage V_{dc} of the edge ring **24**. In other words, the AC voltage applied to each of the electrodes in the second electrode **20c** from the power supply **23** is obtained by superimposing, on an AC component, a negative DC voltage component having a magnitude based on the magnitude of the self-bias voltage V_{dc} of the edge ring **24** (i.e., the AC voltage applied from the power supply **23** to each of the electrodes in the second electrode **20c** is made by offsetting an AC component by the magnitude of the negative DC voltage component based on the self-bias voltage V_{dc} of the edge ring **24**). FIG. **4A** illustrates a case in which the AC voltages applied are offset by -0.2 (i.e., the self-bias voltage V_{dc} of the edge ring **24** is -0.2).

(41) Attractive force generated in the edge ring **24** when two-phase AC voltages illustrated in FIG. **4A** are applied to the electrodes in the second electrode **20c** will be described with reference to FIG. **4B**. FIG. **4B** is a graph illustrating an example of a sum of the attractive force of the edge ring **24** when the two-phase AC voltages are applied to the electrodes in the second electrode **20c**. The vertical axis indicates the sum of the attractive force and the horizontal axis indicates time. As illustrated in FIG. **4B**, even if the number of electrodes in the second electrode **20c** is two, the attractive force by which the mounting table **16** attracts the edge ring **24** can be kept constant.

(42) A method of attracting an object to the mounting table **16** (electrostatic chuck **20**) of the

plasma processing apparatus **1** according to the present embodiment will be described in comparison with reference examples.

(43) An attracting method according to a first reference example will be briefly described. In the attracting method according to the first reference example, DC voltage is applied to each of the first and second electrodes **20a** and **20c** in the electrostatic chuck **20** to attract the wafer **W** and the edge ring **24** to the mounting table **16**. In the method of applying DC voltage, as time when the wafer **W** and the edge ring **24** are attracted to the mounting table **16** increases, electrical charges in the wafer **W** or the edge ring **24** move to the insulating layer **20b** of the electrostatic chuck **20**. Therefore, because the voltage substantially applied between the electrostatic chuck **20** and the wafer **W** or the edge ring **24** decreases, electrostatic attractive force decreases. In addition, during plasma processing, heat of the plasma enters the mounting table **16**. As the temperature of the mounting table **16** increases, it becomes easier for an electrical charge to move. Thus, as the voltage substantially applied between the electrostatic chuck **20** and the wafer **W** or the edge ring **24** further decreases, the electrostatic attractive force further decreases.

(44) In contrast, in the attracting method performed by the mounting table **16** of the plasma processing apparatus **1** according to the present embodiment, by applying AC voltages to the first and second electrodes **20a** and **20c** in the electrostatic chuck **20**, the wafer **W** and the edge ring **24** are attracted to the mounting table **16**. Accordingly, even though the wafer **W** and the edge ring **24** are attracted for a long time, decrease in electrostatic attractive force caused by movement of electrical charge can be prevented.

(45) Next, an attracting method according to a second reference example will be briefly described. In the attracting method according to the second reference example, AC voltages are applied to the first and second electrodes **20a** and **20c** in the electrostatic chuck **20** to attract the wafer **W** and the edge ring **24** to the mounting table **16**. In the second reference example, an average value of each of the AC voltages applied is set to 0 V (ground).

(46) FIGS. 5A and 5B are graphs illustrating examples of a relationship between the applied voltage and a flow rate of a heat transfer gas (He gas). FIG. 5A illustrates a case of the present embodiment, and FIG. 5B illustrates a case of the second reference example. The vertical axis on the left side in the graphs indicates applied voltage, the vertical axis on the right side indicates a flow rate of He gas, which is a heat transfer gas supplied between the upper surface of the electrostatic chuck **20** and the bottom surface of the edge ring **24**, and the horizontal axis indicates time. In the graphs, an example of AC voltage applied to one electrode in the second electrode **20c** is illustrated in a solid line curve, and an example of AC voltage applied to the other electrode in the second electrode **20c** is illustrated in a dashed-dotted line curve. The amplitude of the applied voltage is normalized to 1. Further, a flow rate of He gas is illustrated in a broken line curve. Here, a case in which two-phase AC voltage is applied is described.

(47) During plasma processing, negative self-bias voltage V_{dc} is generated at the edge ring **24**. Thus, in the example of FIG. 5B, a period of time when voltage at an electrode relative to the edge ring **24** is positive is longer than a period of time when voltage at the electrode relative to the edge ring **24** is negative. Also, the maximum absolute value of the voltage at the electrode relative to the edge ring **24** during the period when the voltage is positive is greater than the maximum absolute value of the voltage at the electrode relative to the edge ring **24** during the period when the voltage is negative. Because of these reasons, as in the case of applying DC voltage described in the first reference example, electrical charge on the edge ring **24** moves to the insulating layer **20b** of the electrostatic chuck **20** as time for attracting the edge ring **24** to the mounting table **16** increases. Therefore, as a period of time when the edge ring **24** is attracted to the mounting table **16** increases, the voltage substantial applied decreases, and attractive force of the edge ring **24** decreases. In addition, due to the difference between the average value of the applied AC voltage and an electric potential (voltage relative to the ground) of the edge ring **24** (self-bias voltage V_{dc}), a sum of the attractive force of the edge ring **24** oscillates, and stable attractive force is not obtained.

(48) Here, as the attractive force for attracting the edge ring **24** to the mounting table **16** decreases, a gap between the upper surface of the electrostatic chuck **20** and the back surface of the edge ring **24** increases, and the flow rate of He gas supplied to the gap increases. In a case in which the average value of the applied voltage is 0 V, the flow rate of He gas gradually increases, as indicated by the arrow **502** in FIG. 5B, indicating that the attractive force for attracting the edge ring **24** is decreasing. Also, fluctuation in the flow rate of He gas is greater than that illustrated in FIG. 5A, which will be described below.

(49) In contrast, in the attracting method performed by the plasma processing apparatus **1** according to the present embodiment, as illustrated in FIG. 5A, AC voltages on the basis of the self-bias voltage V_{dc} of the edge ring **24** are applied to the electrodes in the mounting table **16**. In other words, an average value of the applied AC voltage is offset by the self-bias voltage V_{dc} of the edge ring **24**.

(50) Thus, in the example of FIG. 5A, a period of time when voltage at an electrode relative to the edge ring **24** (self-bias voltage V_{dc}) is positive can be made to be equal to a period of time when voltage at the electrode relative to the edge ring is negative. Also, the maximum absolute value of the voltage at the electrode relative to the edge ring **24** during the period when the voltage is positive can be made to be equal to the maximum absolute value of the voltage at the electrode relative to the edge ring **24** during the period when the voltage is negative. Therefore, it is possible to prevent electrical charge on the edge ring **24** from moving to the insulating layer **20b** of the electrostatic chuck **20** even if the time for attracting the edge ring **24** to the mounting table **16** increases. As indicated by the arrow **501** illustrated in FIG. 5A, increase in the flow rate of He gas is suppressed, indicating that decrease in the attractive force for attracting the edge ring **24** is suppressed. Also, fluctuation in the flow rate of He gas is smaller than that illustrated in FIG. 5B.

(51) As described above, according to the attracting method of the mounting table **16** of the plasma processing apparatus **1** according to the present embodiment, even though a period of time when the electrostatic chuck **20** attracts an object (i.e., wafer **W** or edge ring **24**) increases, decrease in attractive force can be suppressed. Accordingly, even in a process of attracting an object (wafer **W**, edge ring **24**) for a long period of time, such as a process of making a 3D NAND device having a large number of layers, decrease in the attractive force can be prevented.

(52) In the above description, a case in which AC voltage applied to each of the electrodes in the second electrode **20c** (or the first electrode **20a**) is obtained by superimposing the self-bias voltage V_{dc} of a negative value (in the example of FIG. 3A, V_{dc} was -0.2) on an AC component has been described. However, DC voltage to be superimposed on an AC component is not limited thereto. For example, negative DC voltage based on the self-bias voltage V_{dc} , such as -0.1 , which is DC voltage having a magnitude of 50% of V_{dc} , may be superimposed on an AC component. Even in this case, because movement of electrical charge can be reduced compared to the case of the second reference example, decrease in attractive force for attracting an object to the electrostatic chuck **20** can be reduced to some extent.

(53) Although the embodiments of the plasma processing apparatus **1** and the like have been described, the present disclosure is not limited to the above-described embodiments, and various modifications and enhancements can be made within the scope of the gist of the present disclosure described in the claims.

Claims

1. A method of attracting at least one object to a mounting table provided with an electrostatic chuck including electrodes, the method comprising: placing the object on the electrostatic chuck; and applying n-phase alternating current (AC) voltages ($n \geq 2$) to the electrodes, each phase voltage of the n-phase AC voltages having a phase different from each other, wherein the at least one object includes a substrate, an edge ring, or a combination of the substrate and the edge ring, and the

- phase voltage of the n-phase AC voltages is applied based on a self-bias voltage of the object.
2. The method according to claim 1, wherein the phase voltage of the n-phase AC voltages is obtained by superimposing, on an AC component, negative direct-current (DC) voltage based on the self-bias voltage of the object.
 3. The method according to claim 2, wherein the self-bias voltage is calculated in accordance with a condition of plasma processing.
 4. The method according to claim 2, wherein the self-bias voltage is detected by a voltage detector configured to detect voltage of the object.
 5. The method according to claim 1, further comprising: estimating the self-bias voltage of the at least one object under a condition in which a plasma is formed, wherein the applying of the n-phase AC voltages to the electrodes is performed such that each AC voltage of the applied AC voltages is offset by the estimated self-bias voltage from a magnitude of the AC voltage.
 6. The method according to claim 1, further comprising: detecting the self-bias voltage of the at least one object, wherein the applying of the n-phase AC voltages to the electrodes is performed using a power supply, such that each AC voltage of the applied AC voltages is offset by the detected self-bias voltage from a magnitude of the AC voltage.
 7. The method according to claim 1, further comprising: preliminarily storing the self-bias voltage of the at least one object in a memory, wherein the applying of the n-phase AC voltages to the electrodes is performed such that each AC voltage of the applied AC voltages is offset by the stored self-bias voltage from a magnitude of the AC voltage.
 8. The method according to claim 1, further comprising: supplying a heat transfer gas to a space between an upper surface of the mounting table and a back surface of the object.
 9. The method according to claim 1, wherein a phase difference between AC voltages of the n-phase AC voltages applied to the electrodes is 120° in a case where n is 3.
 10. The method according to claim 1, wherein a phase difference between the n-phase AC voltages applied to the electrodes is 90° in a case where n is 2.
 11. The method according to claim 1, wherein a magnitude of negative direct-current (DC) voltage applied to the object is the same as that of the self-bias voltage of the object.
 12. The method according to claim 1, wherein the method of attracting at least one object to a table is performed using an etching apparatus.
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